

No. M15-iv Pb_{1-x}Ge_xTe

1b	The system Pb _{1-x} Ge _x Te forms a solid solution over the whole range of x, and shows a structural phase transition from cubic to rhombohedral phase. Transition temperature as a function of composition x: Fig. M15-iv-001; see also	72Hoh, 82Mas, 84Tak, 91Ser
	Phase diagram for pressure and composition: see	
3a	Unit cell parameters, see	91Ser
4	Lattice distortions: Fig. M15-iv-002, Fig. M15-iv-003; see also	88Koz
5a	Dielectric constants: at 10 MHz (impedance), see at 50 GHz, see at optical frequency, see	82Mas 81Mur, 79Mur, 80Jan, 87Abd
	Capacitance data on p-n junction diodes: see	73Ant, 80Gri
6a	Heat capacity: see	81Sug
8	Elastic properties: c_{11} , c_{12} and c_{44} obtained by ultrasonic measurements: see	79Sug
9a	Absorption coefficients: see	80Jan, 81Glo
	Band gap vs. T : Fig. M15-iv-004; see also	82Luc
	Reflection spectra: Fig. M15-iv-005; see also	70Sob
10a	Raman scattering, soft TO phonon modes: see	79Sug, 79Mur
11	Electrical resistivity: see	79Tak, 83Abd, 84Tak, 84Kum
	Hydrostatic pressure effects on resistivity: Fig. M15-iv-006; see also	84Sus
	Magnetic field effects on resistivity: see	89Pav
	Charge carrier mobility (n-type): see	80Las, 85Gra, 93Rog
	Effects of carrier concentration under illumination on the transition temperature: see	82Mas
	Magnetooptic investigation of band structure: see	85Ban
14c	EXAFS: see	87Isl, 91Bun